

# NPN RF POWER TRANSISTOR

**DESCRIPTION:**

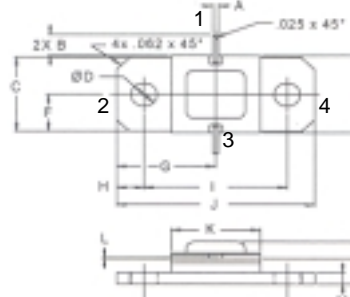
The **ASI MS2601** is Common Base Device Designed for Pulsed S-Band Radar Amplifier Applications up to 3.1 GHz.

**FEATURES INCLUDE:**

- Input/Output Matching
- Gold Metallization
- Emitter Ballasting

**MAXIMUM RATINGS**

$I_C$	0.45 A
$V_{CC}$	34 V
$P_{DISS}$	11.5 W @ $T_C = 25^\circ\text{C}$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	13.0 °C/W

**PACKAGE STYLE 400 x 400 2NL FLG**


DIM	MINIMUM Inches / mm	MAXIMUM Inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F		.193 / 4.90
G		.450 / 11.43
H		.125 / 3.18
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.084 / 0.10	.097 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.116 / 3.00	.131 / 3.33
P		.230 / 5.84

1 = COLLECTOR    2 & 4 = BASE  
3 = EMITTER

**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 1.0\text{ mA}$	45			V
$BV_{CER}$	$I_C = 1.0\text{ mA}$	45			V
$BV_{EBO}$	$I_E = 1.0\text{ mA}$	3.5			V
$I_{CES}$	$V_{CE} = 30\text{ V}$			0.5	mA
$h_{FE}$	$V_{CE} = 5\text{ V}$ $I_C = 100\text{ mA}$	10		150	---
$P_{OUT}$	$V_{CC} = 30\text{ V}$ $P_{IN} = 0.3\text{ W}$ $f = 2700\text{ to }3100\text{ MHz}$	1.0			W
$P_G$	Pulse Width = 100 $\mu\text{S}$ Duty Cycle = 10%	5.2			dB
$\eta_c$		27			%